



# 30V N-Channel Power MOSFET

TO-252 (DPAK)

# 2 65 2 3

#### Pin Definition:

- 1. Gate
- 2. Drain
- 3. Source

## **Key Parameter Performance**

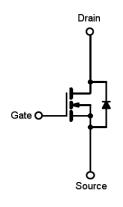
Parameter		Value	Unit	
$V_{DS}$		30	V	
R <sub>DS(on)</sub> (max)	$V_{GS} = 10V$	4	mΩ	
	$V_{GS} = 4.5V$	6		
$Q_{g}$		24	nC	

### **Ordering Information**

Ordering code	Package	Packing		
TSM040N03CP ROG	TO-252	2.5kpcs / 13" Reel		
Note: Hologon from according to IEC 04240-2-24 definition				

**Note:** Halogen-free according to IEC 61249-2-21 definition

### **Block Diagram**



N-Channel MOSFET

### **Absolute Maximum Ratings** (T<sub>C</sub>=25°C unless otherwise noted)

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		$V_{DS}$	30	V
Gate-Source Voltage		$V_{GS}$	±20	V
Continuous Drain Current	T <sub>C</sub> =25°C	1	90	А
Continuous Drain Current	T <sub>C</sub> =100°C	l <sub>D</sub>	57	А
Pulsed Drain Current (Note 1)		I <sub>DM</sub>	360	А
Single Pulse Avalanche Energy (Note 2)		E <sub>AS</sub>	125	mJ
Single Pulse Avalanche Current (Note 2)		I <sub>AS</sub> 50		А
Total Power Dissipation	@ T <sub>C</sub> =25°C	T <sub>C</sub> =25°C		W
	Derate above T <sub>C</sub> =25°C	$P_{D}$	0.59	W/ºC
Operating Junction Temperature		TJ	150	°C
Storage Temperature Range		T <sub>STG</sub> -55 to +150		°C

### **Thermal Performance**

Parameter	Symbol	Limit	Unit
Thermal Resistance - Junction to Case	$R_{\Theta JC}$	1.7	°C/W
Thermal Resistance - Junction to Ambient	$R_{\Theta JA}$	62	°C/W



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**Electrical Specifications** (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Тур	Max	Unit
Static					•	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV <sub>DSS</sub>	30			V
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 24A$	_		3.1	4	mΩ
	$V_{GS} = 4.5V, I_D = 12A$	$R_{DS(ON)}$		4.5	6	
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	V <sub>GS(TH)</sub>	1.2	1.6	2.5	V
	$V_{DS} = 30V, V_{GS} = 0V$				1	μΑ
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 24V, T <sub>J</sub> = 125°C	- I <sub>DSS</sub>			10	
Gate Body Leakage	$V_{GS} = \pm 20V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Forward Transconductance	$V_{DS} = 10V, I_{D} = 10A$	g <sub>fs</sub>		15.5		S
Dynamic						
Total Gate Charge (Note 3,4)		$Q_g$		24		nC
Gate-Source Charge (Note 3,4)	$V_{DS} = 15V, I_{D} = 24A,$	$Q_gs$		4.2		
Gate-Drain Charge (Note 3,4)	$V_{GS} = 4.5V$	$Q_gd$		13		
Input Capacitance		C <sub>iss</sub>		2200		
Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V,$	C <sub>oss</sub>		280		pF
Reverse Transfer Capacitance	f = 1MHz	C <sub>rss</sub>		177		-
Gate Resistance	f = 1MHz	$R_g$		2		Ω
Switching						
Turn-On Delay Time (Note 3,4)		t <sub>d(on)</sub>		12.6		
Turn-On Rise Time (Note 3,4)	V <sub>DD</sub> =15V , V <sub>GS</sub> =10V ,	t <sub>r</sub>		19.5		
Turn-Off Delay Time (Note 3,4)	$R_G=3.3\Omega$ , $I_D=-15A$	t <sub>d(off)</sub>		42.8		ns
Turn-Off Fall Time (Note 3,4)		t <sub>f</sub>		13.2		
Source-Drain Diode Ratings and C	haracteristic	•				•
Continuous Drain-Source Diode		Is			90	Α
Pulse Drain-Source Diode		I <sub>SM</sub>			360	Α
Diode-Source Forward Voltage	$V_{GS} = 0V, I_{S} = 1A$	V <sub>SD</sub>			1	V
	•	•		•	•	•

2/5

### Note:

- 1. Repetitive Rating: Pulsed width limited by maximum junction temperature.
- 2.  $V_{DD}$ =25V,  $V_{GS}$ =10V, L=0.1mH,  $I_{AS}$ =50A,  $R_{G}$ =25 $\Omega$ , Starting  $T_{J}$ =25 $^{\circ}$ C
- 3. The data tested by pulsed, pulse width ≤300µs, duty cycle ≤2%
- 4. Essentially independent of operating temperature.

Version: B1807

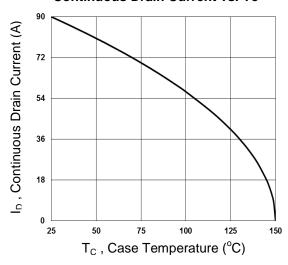


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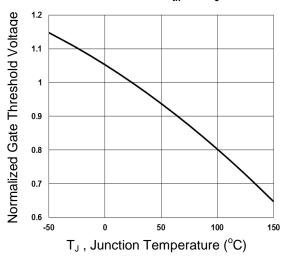
# Pb ROHS COMPLIANT

### **Electrical Characteristics Curves**

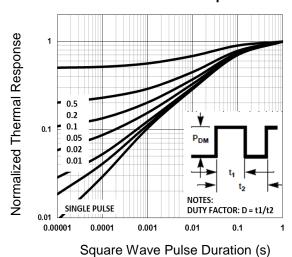
### Continuous Drain Current vs. Tc



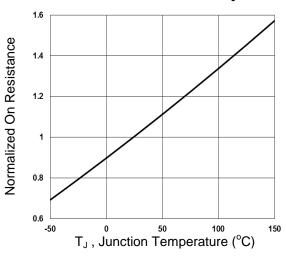
### Normalized $V_{th}$ vs. $T_J$



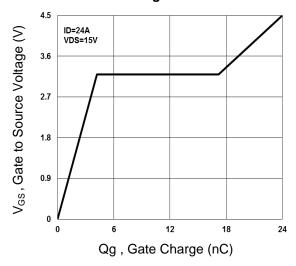
### **Normalized Transient Impedance**



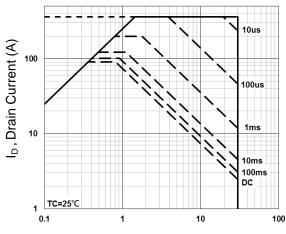
Normalized RDSON vs. T<sub>J</sub>



**Gate Charge Waveform** 



**Maximum Safe Operation Area** 



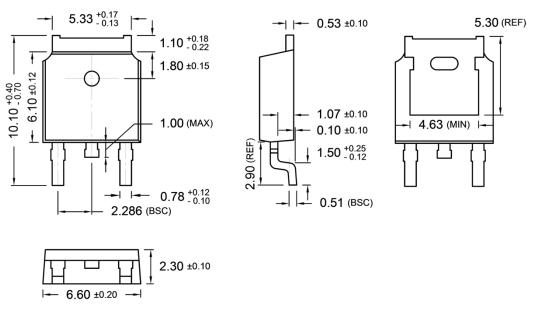
V<sub>DS</sub>, Drain to Source Voltage (V)



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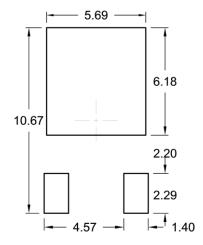


# **TO-252 Mechanical Drawing**



Unit: Millimeters

### **SUGGESTED PAD LAYOUT** (Unit: Millimeters)



# **Marking Diagram**





# TSM040N03CP 30V N-Channel Power MOSFET

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